

# 5.0x6.0mm FULL COLOR LED LAMP

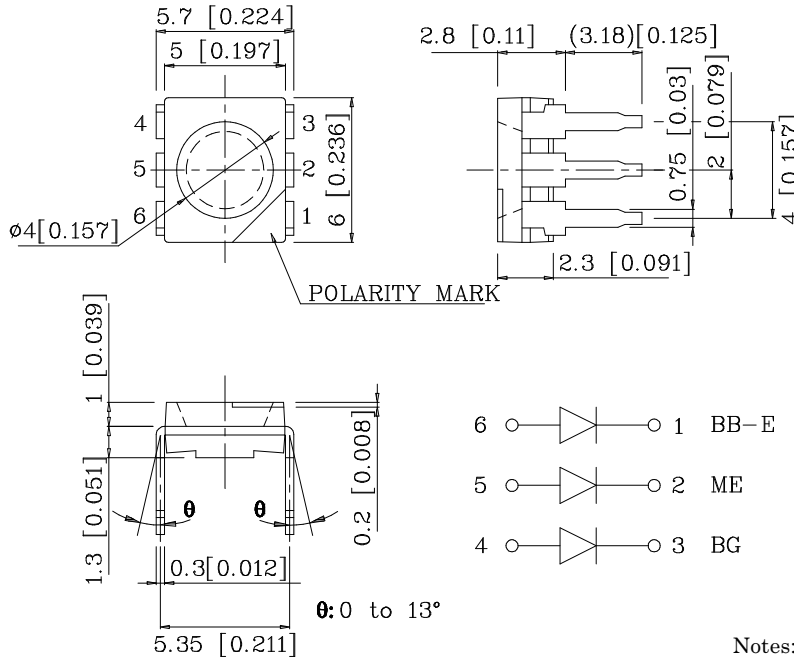


# SUN LED

XSBBEMEBG99W

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Web Site : www.sunled.com



**ATTENTION**  
 OBSERVE PRECAUTIONS  
 FOR HANDLING  
 ELECTROSTATIC  
 DISCHARGE  
 SENSITIVE  
 DEVICES

Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is  $\pm 0.25(0.01)$ " unless otherwise noted.

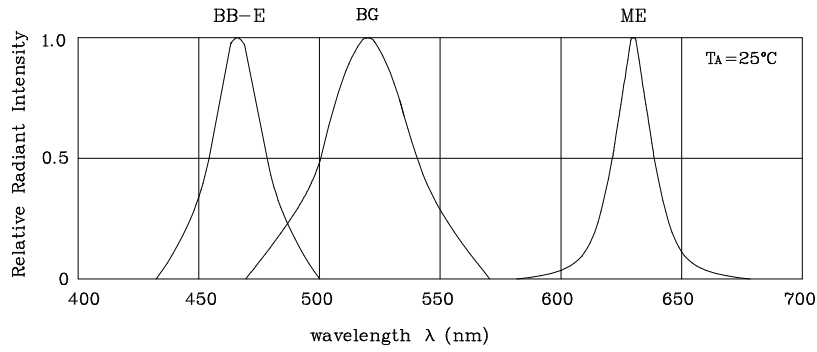
Absolute maximum ratings ( $T_A=25^\circ\text{C}$ )		BB-E (InGa-N)	ME (InGaAlP)	BG (InGa-N)	Unit
Reverse voltage	$V_R$	5	5	5	V
Forward current	$I_F$	30	50	30	mA
Forward current (peak) 1/10Duty cycle 0.1ms pulse width	$i_{FS}$	160	195	150	mA
Total Power dissipation Within 350mW at all chips are lightened	$P_T$	350			mW
Operating temperature	$T_A$	-40 ~ +85			°C
Storage temperature	$T_{stg}$	-40 ~ +85			
Lead solder temperature [2mm below package base]		260°C For 5 Seconds			

Operating Characteristics ( $T_A=25^\circ\text{C}$ )		BB-E (InGaN)	ME (InGaAlP)	BG (InGaN)	Unit
Forward voltage (typ.) ( $I_F=20\text{mA}$ )	$V_F$	3.7	2.0	3.5	V
Forward voltage (max.) ( $I_F=20\text{mA}$ )	$V_F$	4.3	2.5	4.5	V
Reverse current ( $V_R=5\text{V}$ )	$I_R$	10	10	10	$\mu\text{A}$
Wavelength at peak emission ( $I_F=20\text{mA}$ )	$\lambda_{peak}$	465	630	520	nm
Wavelength at Dominate emission ( $I_F=20\text{mA}$ )	$\lambda_D$	470	621	525	nm
Spectral Line half- width ( $I_F=20\text{mA}$ )	$\Delta\lambda$	25	20	38	nm
Capacitance ( $V_F=0\text{V}$ , $f=1\text{MHz}$ )	$C$	110	25	45	pF

Part Number	Emitting Color	Emitting Material	Lens-color	Luminous Intensity ( $I_F=30 \text{ * } 50\text{mA}$ ) mcd		Wavelength nm $\lambda_P$	Viewing Angle $2\theta_{1/2}$
				min.	typ.		
XSBBEMEBG99W	Blue	InGaN	Water Clear	110	248	465	100°
	Red	InGaAlP		*650	*998	630	
	Green	InGaN		180	348	520	

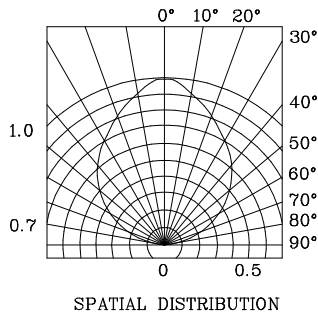
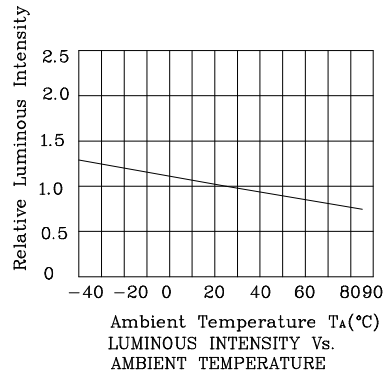
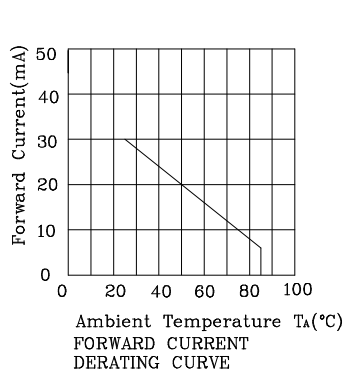
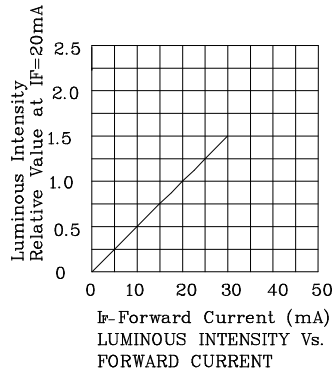
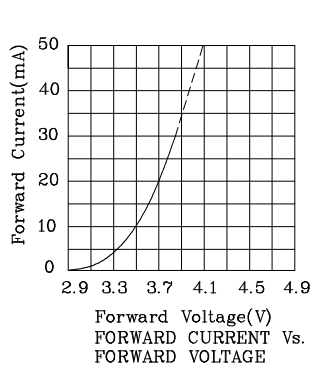
Note: \* Luminous intensity with asterisk is measured at 50mA.

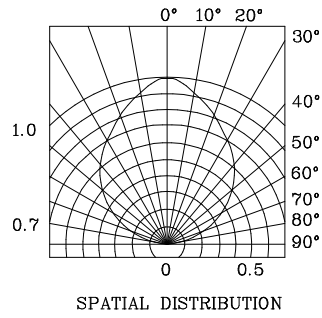
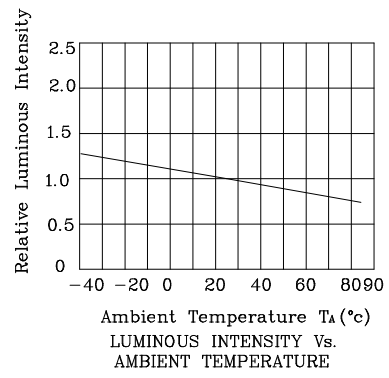
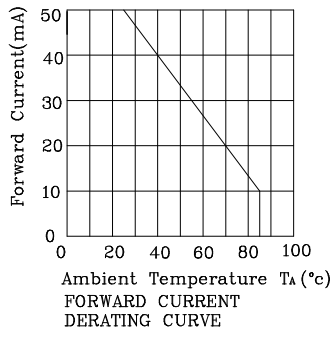
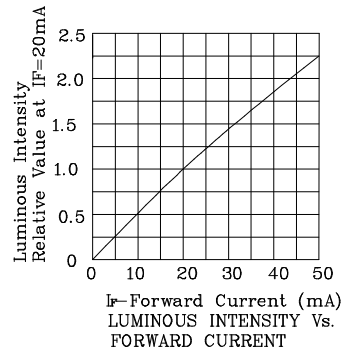
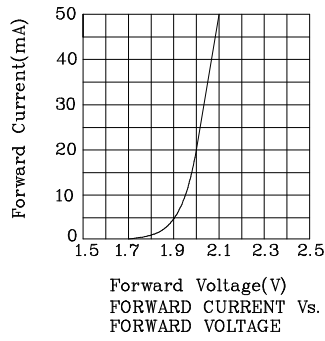
**XSBEMEBG99W**

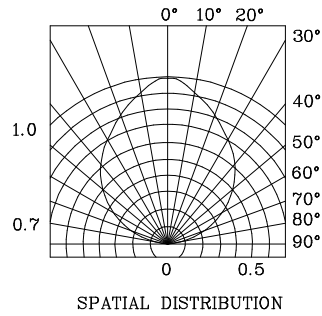
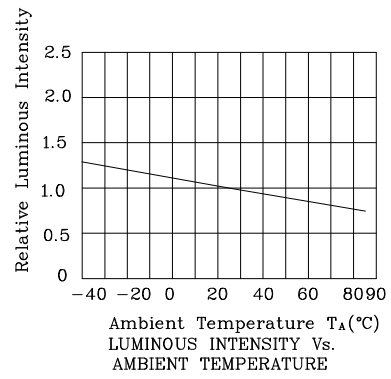
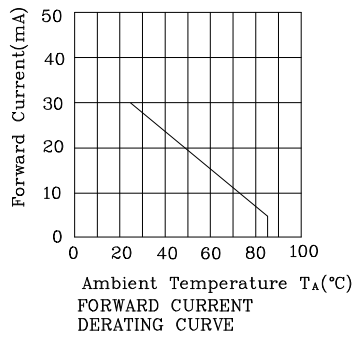
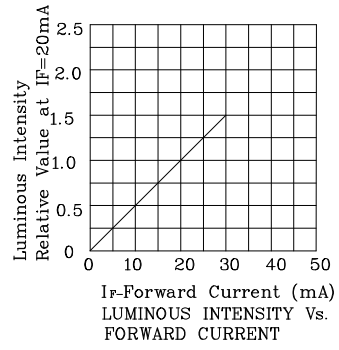
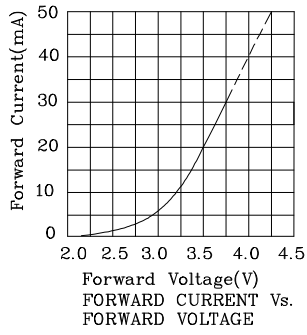


RELATIVE INTENSITY Vs. WAVELENGTH

❖ **BB-E**







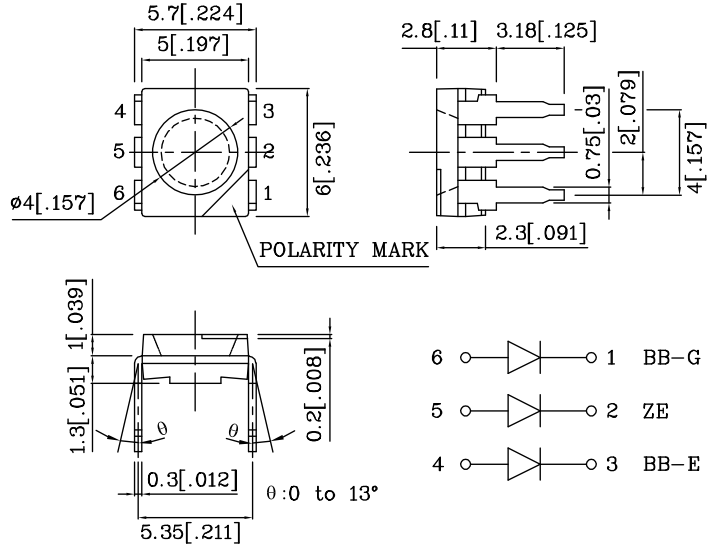
PRELIMINARY SPEC

**Features**

- OUTSTANDING MATERIAL EFFICIENCY.
- RELIABLE AND RUGGED.
- WATER CLEAR LENS.
- LOW POWER CONSUMPTION.
- ONE BLUE, ONE ORANGE AND ONE GREEN CHIPS IN ONE PACKAGE.
- CAN PRODUCE ANY COLOR IN VISIBLE SPECTRUM, INCLUDING WHITE LIGHT.



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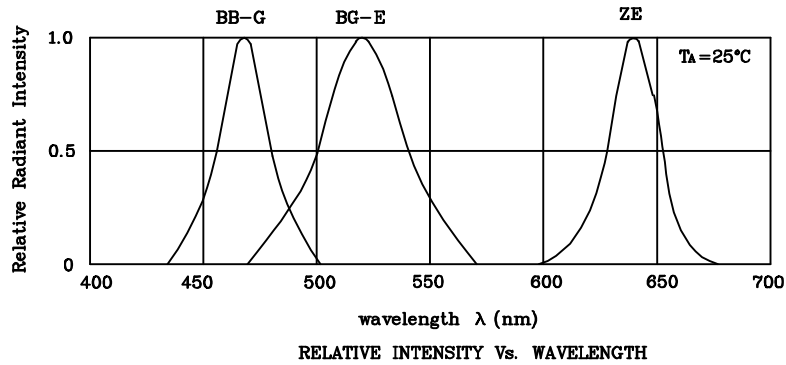
Notes:

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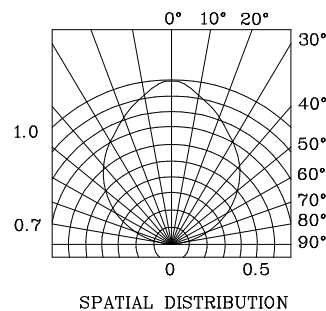
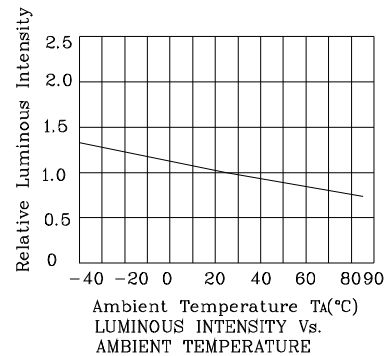
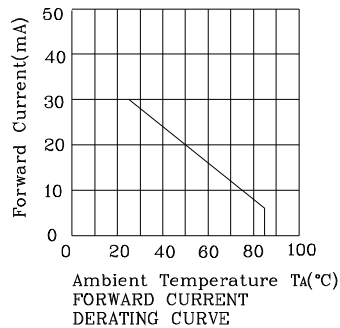
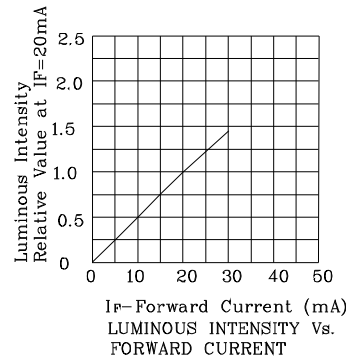
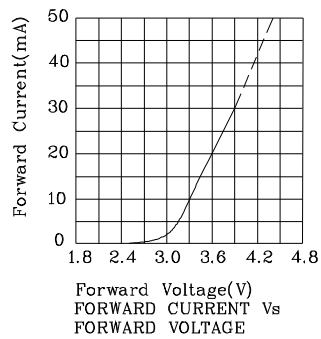
Absolute maximum ratings (TA=25°C)		BB-G (InGaN)	ZE (InGaAlP)	BG-E (InGaN)	Unit
Reverse voltage	VR	5	5	5	V
Forward current	IF	30	50	30	mA
Forward current (peak) 1/10Duty cycle 0.1ms pulse width	iFS	150	150	150	mA
Total Power dissipation Within 350mW at all chips are lightened	PT	350			mW
Operating temperature	TA	-40 ~ +85			°C
Storage temperature	Tstg	-40 ~ +85			

Operating Characteristics (TA=25°C)		BB-G (InGaN)	ZE (InGaAlP)	BG-E (InGaN)	Unit
Forward voltage (typ.) (IF=20mA)	VF	3.6	2.2	3.5	V
Forward voltage (max.) (IF=20mA)	VF	4.3	2.8	4.5	V
Reverse current (VR=5V)	IR	10	10	10	uA
Wavelength at peak emission (IF=20mA)	$\lambda$ peak	468	640	518	nm
Wavelength at Dominate emission (IF=20mA)	$\lambda$ D	470	630	525	nm
Spectral Line half- width (IF=20mA)	$\Delta\lambda$	26	25	36	nm
Capacitance (VF=0V, f=1MHz)	C	110	27	50	pF

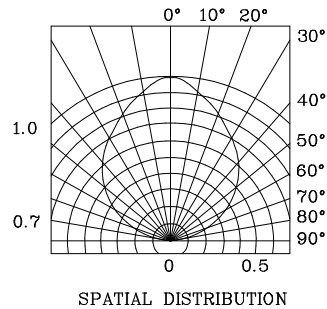
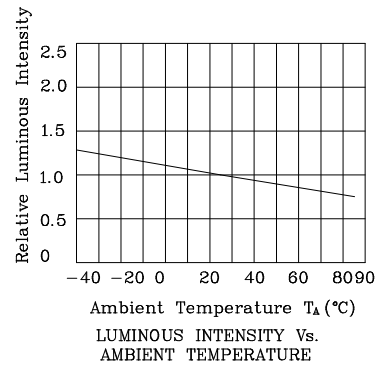
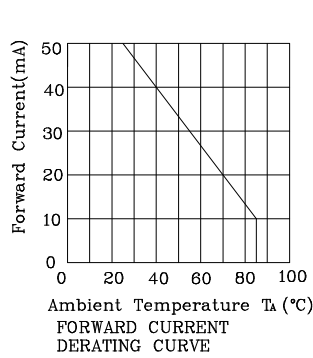
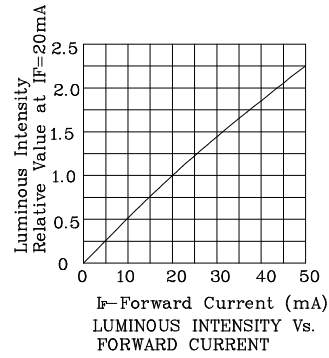
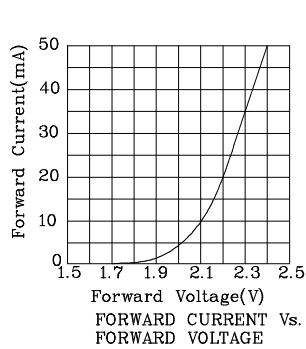
Part Number	Emitting Color	Emitting Material	Lens-color	Luminous Intensity (IF=30mA *50mA) med		Wavelength nm $\lambda$ P	Viewing Angle 2 $\theta$ 1/2
				min.	typ.		
XSBBGZEBGE99W	Blue	InGaN	Water Clear	180	298	468	100°
	Red	InGaAlP		*1500	*2298	640	
	Green	InGaN		280	598	518	



❖ **BB-G**



❖ ZE



❖ BG-E

